

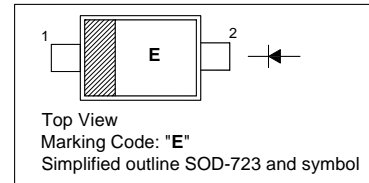
RB521G-30G

Silicon Epitaxial Planar Schottky Barrier Diode

for rectifying small power application

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	30	V
Average Rectified Forward Current	I_O	100	mA
Peak Forward Surge Current (60 Hz for 1 cyc.)	I_{FSM}	1	A
Junction Temperature	T_j	125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 40 to + 125	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 10\text{ mA}$	V_F	0.35	V
Reverse Current at $V_R = 10\text{ V}$	I_R	10	μA

Note: Please pay attention to static electricity when handling.

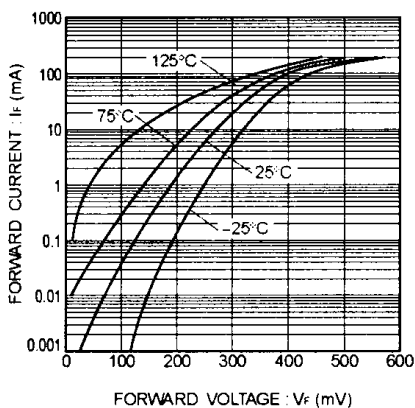


Fig.1 Forward characteristics

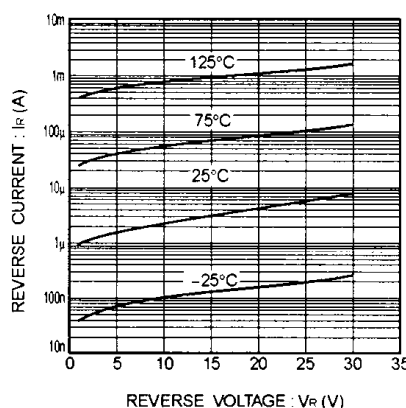


Fig.2 Reverse characteristics

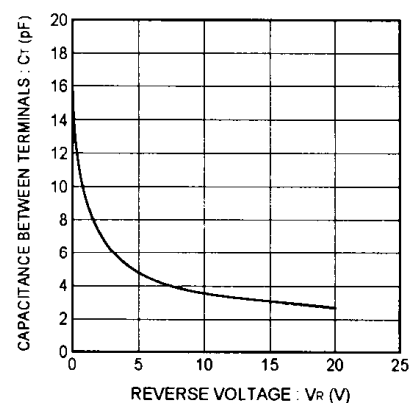
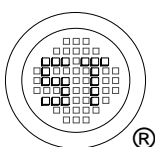


Fig.3 Capacitance between terminals characteristics



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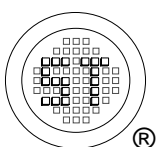
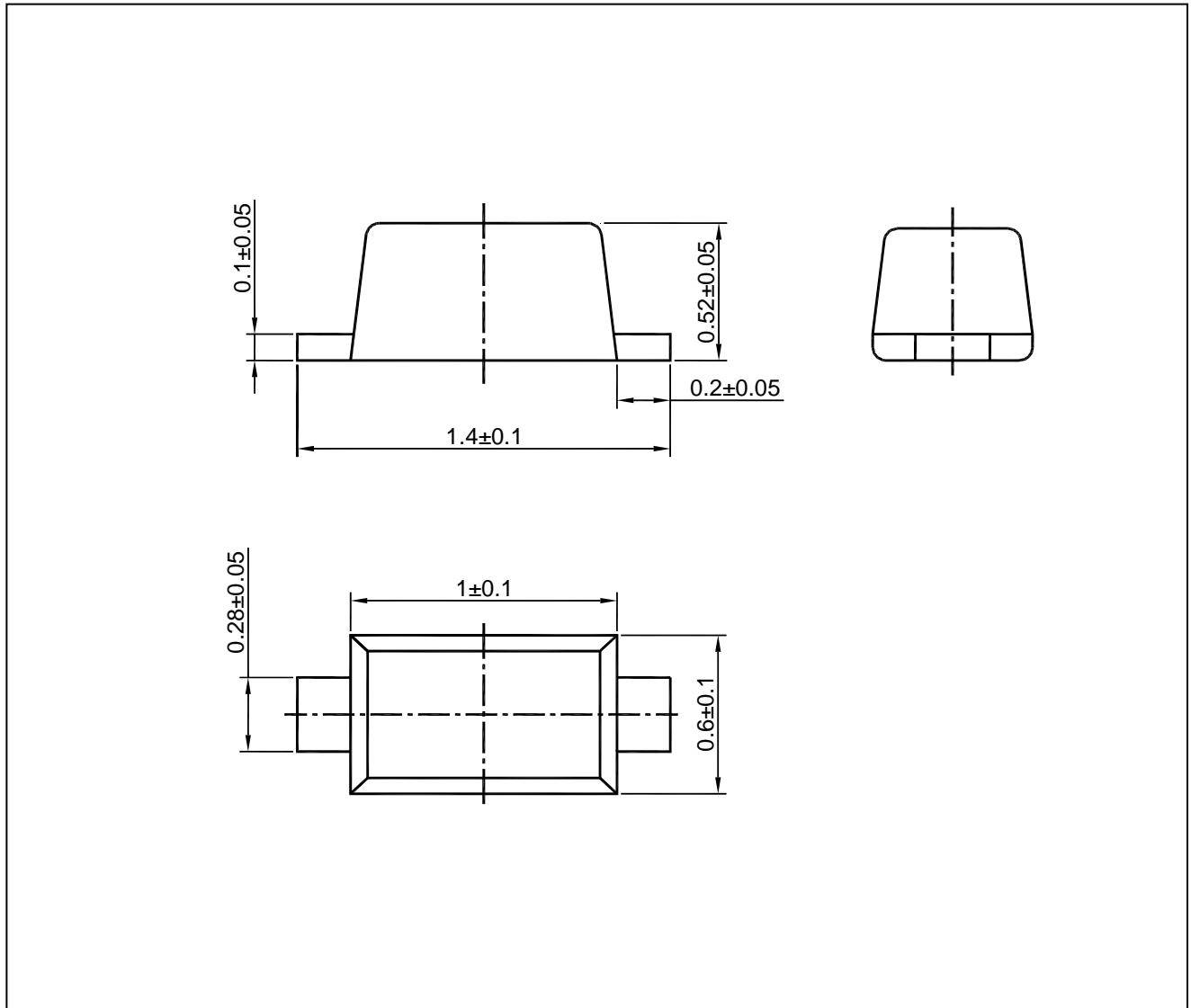


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PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-723



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Dated : 28/07/2010 Rev:01